

Fig. 1 (a)

Side surface

Roughening

13a

13

13a

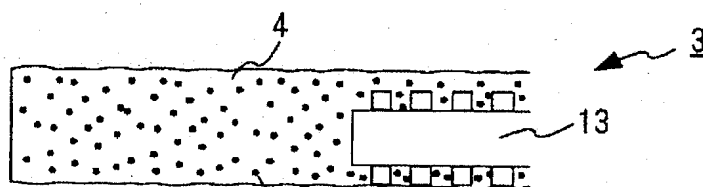


Fig. 1 is a cross-sectional view of a first embodiment of a semiconductor device. It shows a substrate 3 with a semiconductor layer 4a on top. A gate electrode 13 is formed on the semiconductor layer 4a, with gate insulating layers 13a on either side.

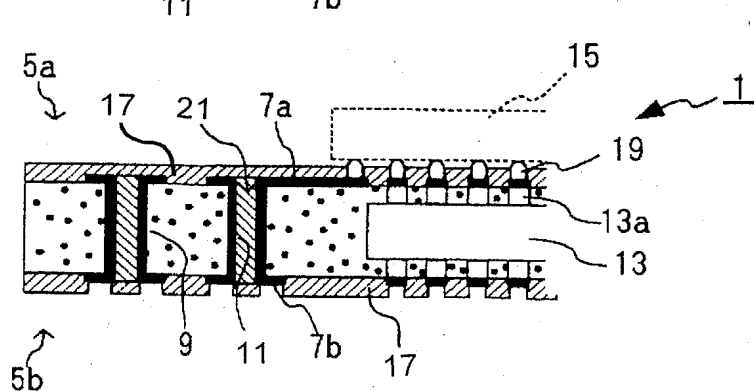
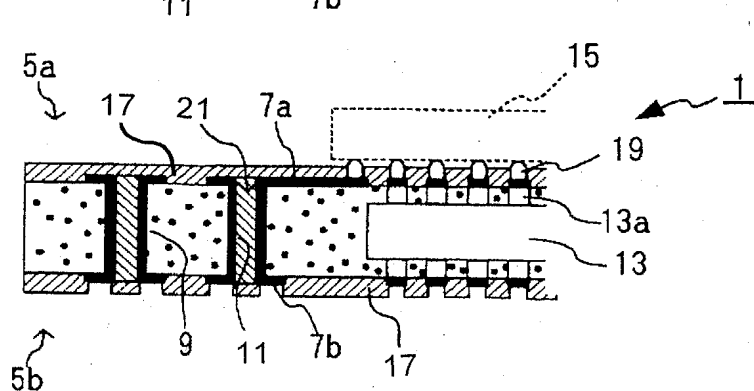
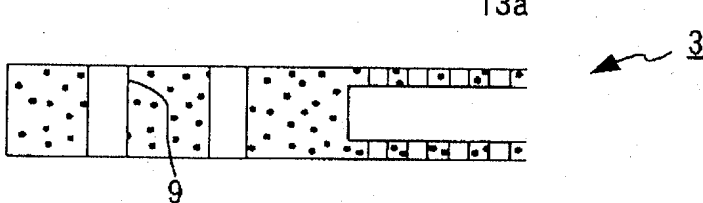
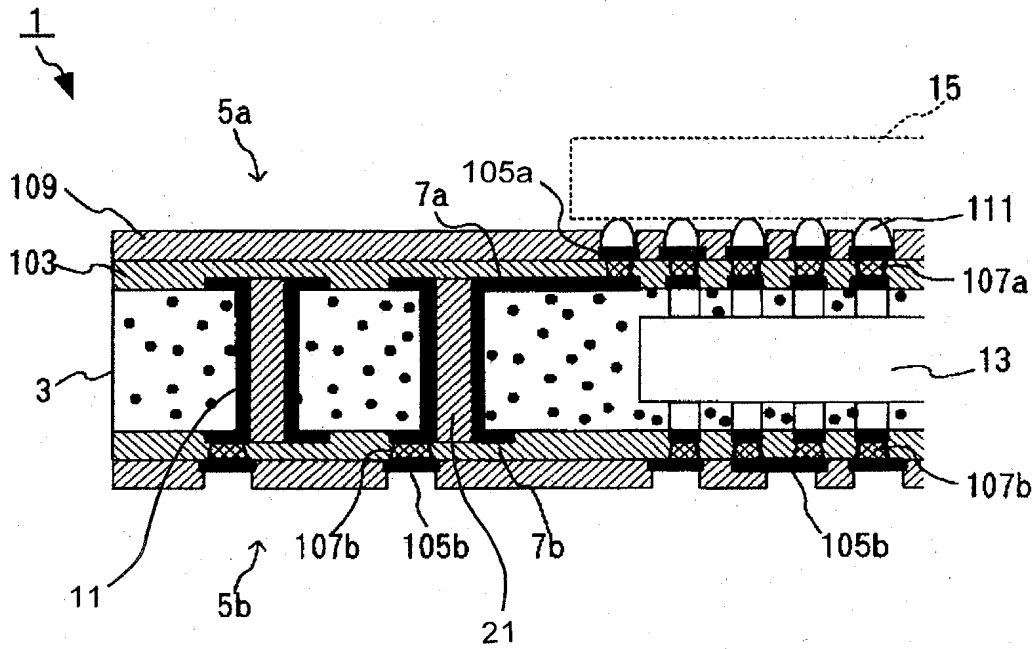


Fig. 2



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Fig. 3 (a)

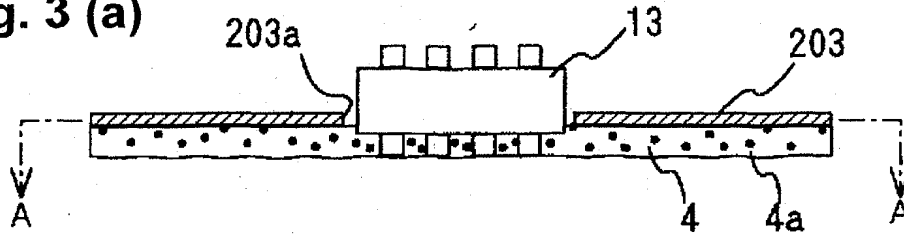


Fig. 3 (b)

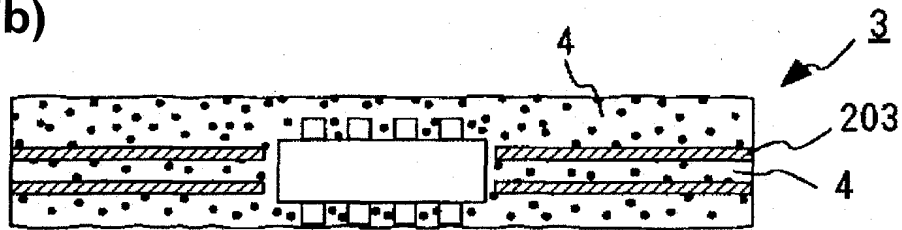
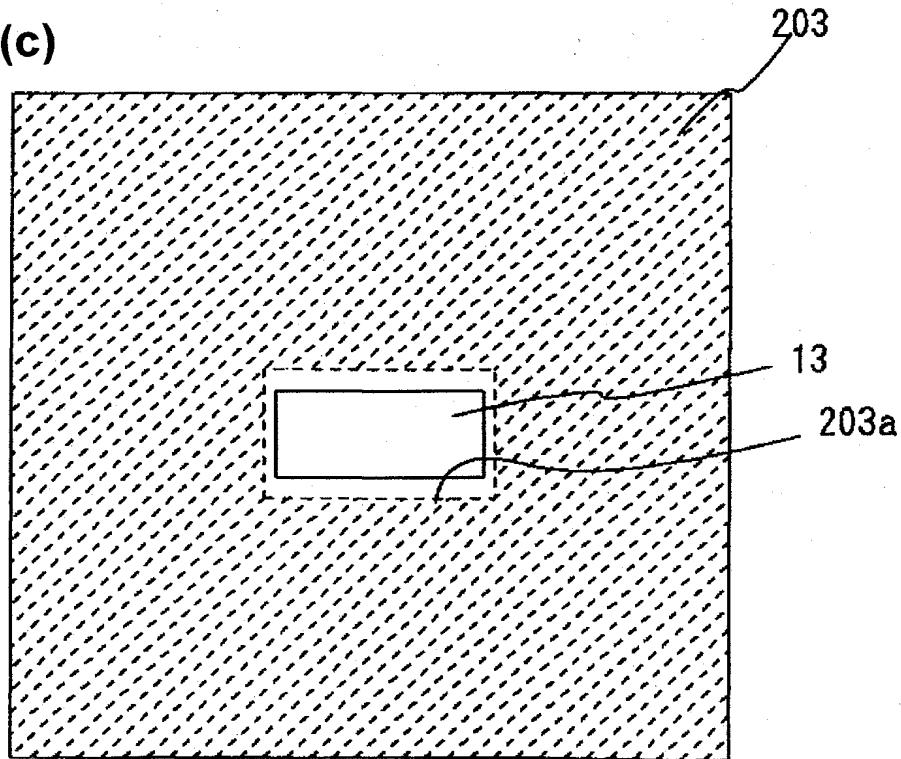


Fig. 3 (c)



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Fig. 4

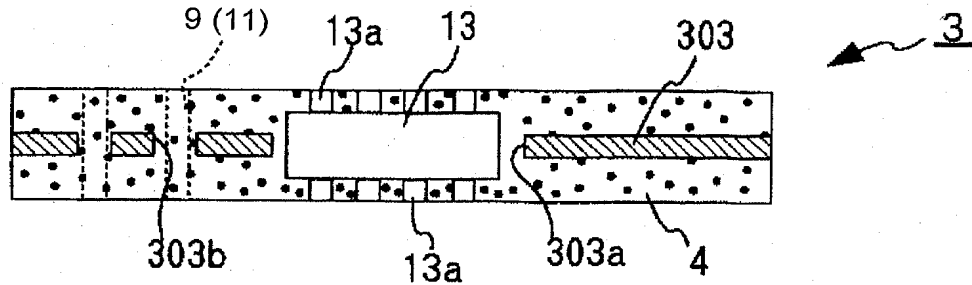


Fig. 5(a)

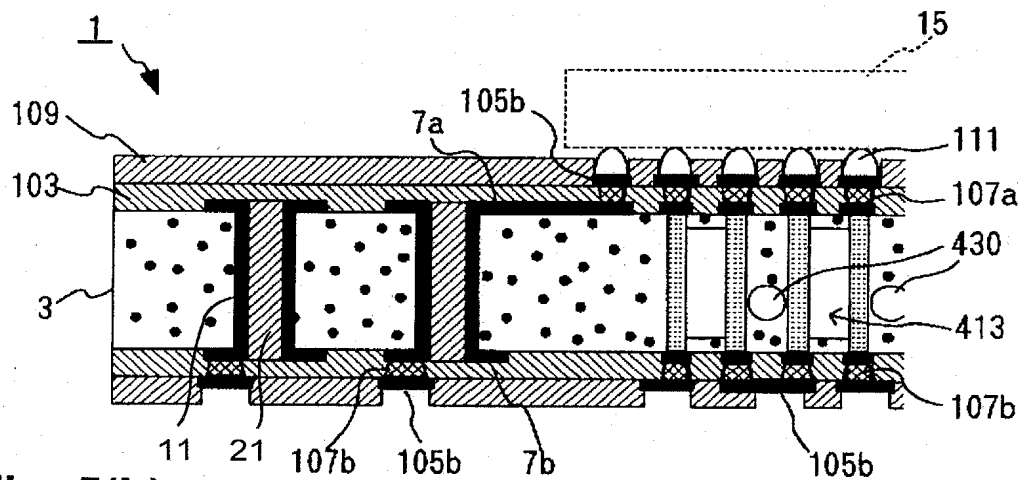


Fig. 5(b)

